

FFSB10120A

Silicon Carbide Schottky Diode

1200 V, 10 A

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 100 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

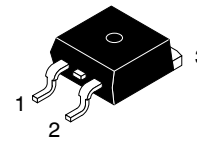
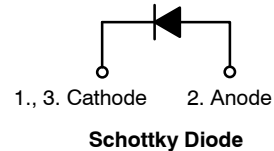
Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits



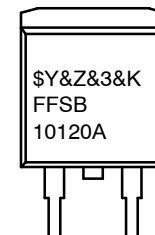
ON Semiconductor®

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**D²PAK-3 (TO-263, 3-LEAD)
CASE 418AJ**

MARKING DIAGRAM



| | |
|------------|-------------------------|
| \$Y | = ON Semiconductor Logo |
| &Z | = Assembly Plant Code |
| &3 | = Numeric Date Code |
| &K | = Lot Code |
| FFSB10120A | = Specific Device Code |

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

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ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

| Symbol | Parameter | Value | Unit | |
|-----------------------------------|---|--|------|---|
| V _{RRM} | Peak Repetitive Reverse Voltage | 1200 | V | |
| E _{AS} | Single Pulse Avalanche Energy (Note 1) | 100 | mJ | |
| I _F | Continuous Rectified Forward Current @ T _C < 164°C | 10 | A | |
| | Continuous Rectified Forward Current @ T _C < 135°C | 21 | | |
| I _{F, Max} | Non-Repetitive Peak Forward Surge Current | T _C = 25°C, 10 μs | 850 | A |
| | | T _C = 150°C, 10 μs | 800 | A |
| I _{F, SM} | Non-Repetitive Forward Surge Current | Half-Sine Pulse, t _p = 8.3 ms | 90 | A |
| I _{F, RM} | Repetitive Forward Surge Current | Half-Sine Pulse, t _p = 8.3 ms | 35 | A |
| P _{tot} | Power Dissipation | T _C = 25°C | 283 | W |
| | | T _C = 150°C | 47 | W |
| T _J , T _{STG} | Operating and Storage Temperature Range | -55 to +175 | °C | |
| | TO-247 Mounting Torque, M3 Screw | 60 | Ncm | |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. E_{AS} of 100 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 20 A, V = 50 V.

THERMAL CHARACTERISTICS

| Symbol | Parameter | Value | Unit |
|------------------|---|-------|------|
| R _{θJC} | Thermal Resistance, Junction to Case, Max | 0.53 | °C/W |

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

| Symbol | Parameter | Test Condition | Min | Typ | Max | Unit |
|----------------|-------------------------|---|-----|------|------|------|
| V _F | Forward Voltage | I _F = 10 A, T _C = 25°C | - | 1.45 | 1.75 | V |
| | | I _F = 10 A, T _C = 125°C | - | 1.7 | 2.0 | |
| | | I _F = 10 A, T _C = 175°C | - | 2.0 | 2.4 | |
| I _R | Reverse Current | V _R = 1200 V, T _C = 25°C | - | - | 200 | μA |
| | | V _R = 1200 V, T _C = 125°C | - | - | 300 | |
| | | V _R = 1200 V, T _C = 175°C | - | - | 400 | |
| Q _C | Total Capacitive Charge | V = 800 V | - | 62 | - | nC |
| C | Total Capacitance | V _R = 1 V, f = 100 kHz | - | 612 | - | pF |
| | | V _R = 400 V, f = 100 kHz | - | 58 | - | |
| | | V _R = 800 V, f = 100 kHz | - | 47 | - | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

| Part Number | Top Marking | Package | Shipping |
|-------------|-------------|--|-------------------|
| FFSB10120A | FFSB10120A | D ² PAK-3 (Pb-Free / Halogen Free) | 800 / Tape & Reel |

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TYPICAL CHARACTERISTICS

($T_J = 25^\circ\text{C}$ unless otherwise noted)

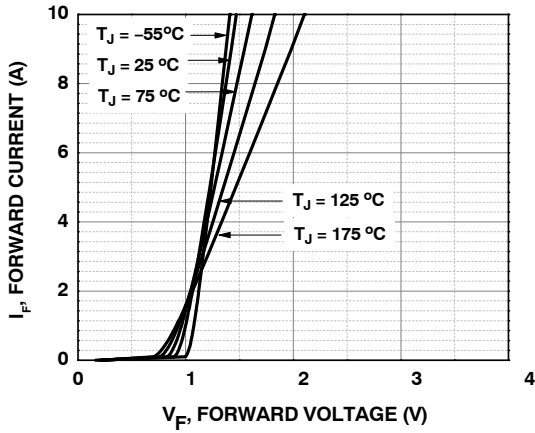


Figure 1. Forward Characteristics

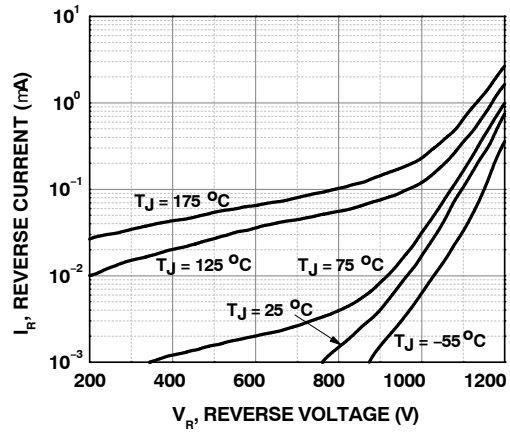


Figure 2. Reverse Characteristics

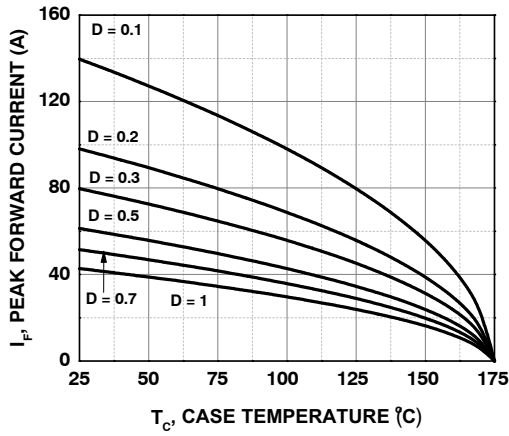


Figure 3. Current Derating

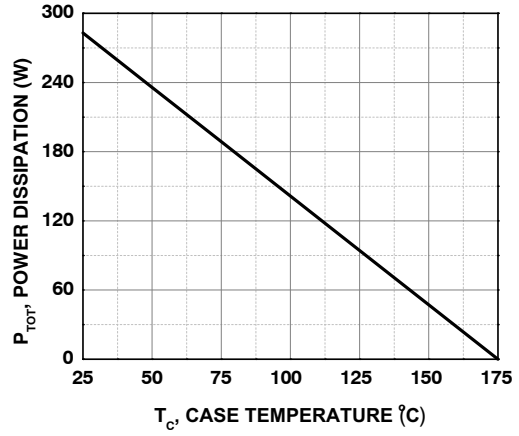


Figure 4. Power Derating

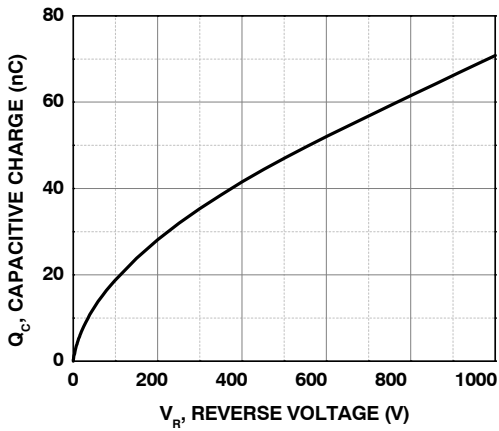


Figure 5. Capacitive Charge vs. Reverse Voltage

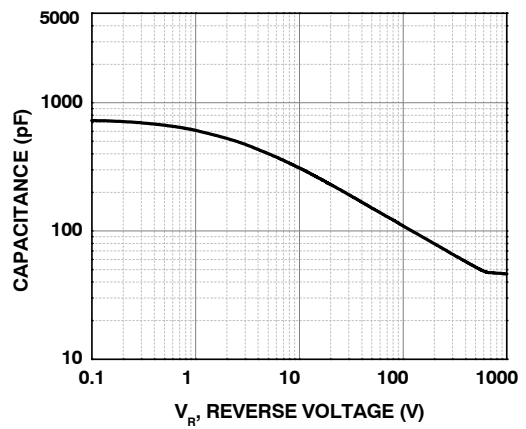


Figure 6. Capacitance vs. Reverse Voltage

TYPICAL CHARACTERISTICS

($T_J = 25^\circ\text{C}$ unless otherwise noted)

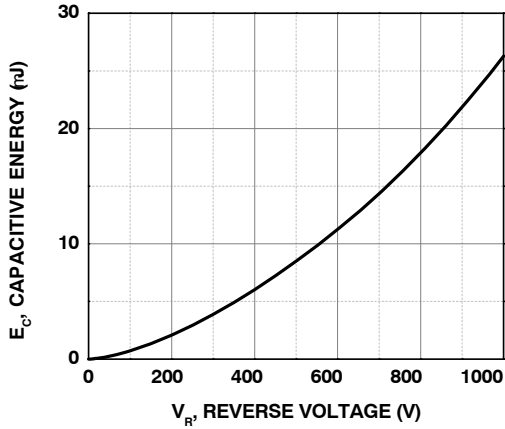


Figure 7. Capacitance Stored Energy

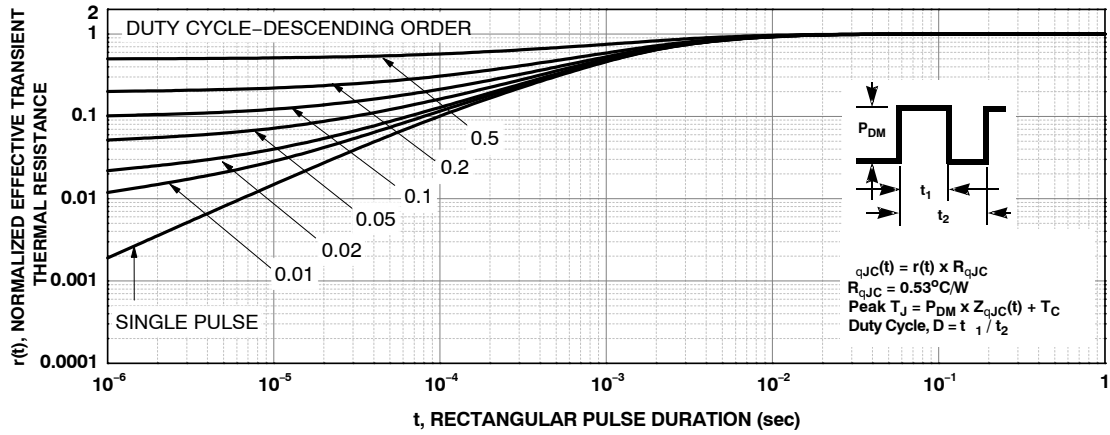


Figure 8. Junction-to-Case Transient Thermal Response Curve

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TEST CIRCUIT AND WAVEFORMS

$L = 0.5 \text{ mH}$
 $R < 0.1 \Omega$
 $V_{DD} = 50 \text{ V}$
 $E_{AVL} = 1/2LI^2 [V_{R(AVL)} / (V_{R(AVL)} - V_{DD})]$
 $Q1 = \text{IGBT} (BV_{CES} > \text{DUT } V_{R(AVL)})$

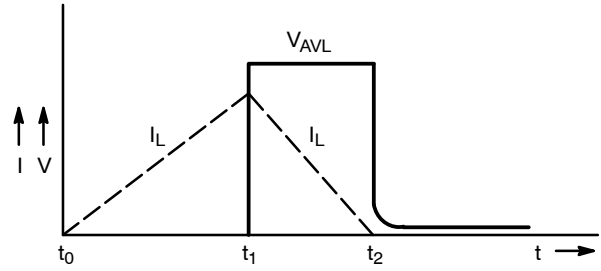
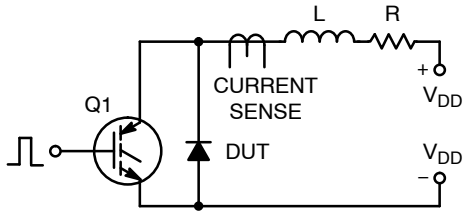
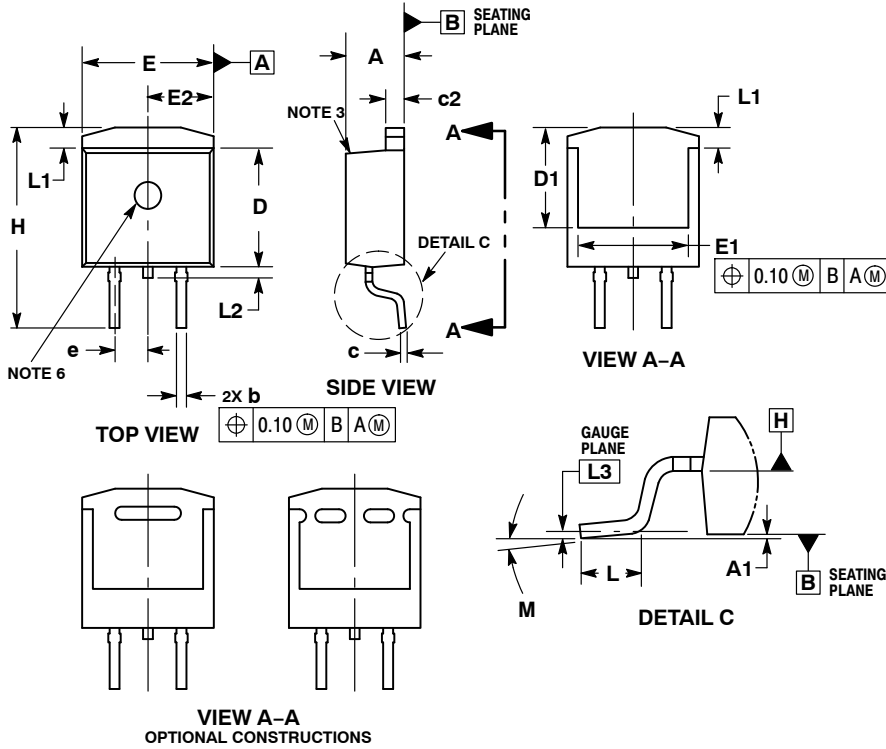


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

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PACKAGE DIMENSIONS

D²PAK-3 (TO-263, 3-LEAD)
CASE 418AJ
ISSUE B

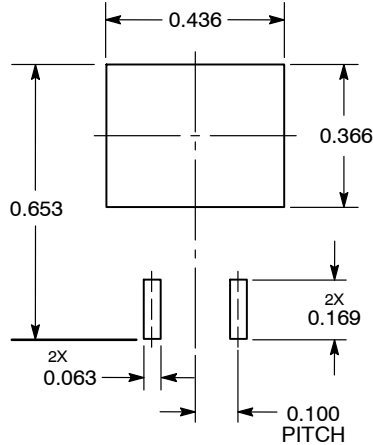


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. CHAMFER OPTIONAL
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
5. THERMAL PAD CONTOUR IS OPTIONAL WITHIN DIMENSIONS E, L1, D1 AND E1.
6. OPTIONAL MOLD FEATURE


| DIM | INCHES | | MILLIMETERS | |
|-----|-----------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.160 | 0.190 | 4.06 | 4.83 |
| A1 | 0.000 | 0.010 | 0.00 | 0.25 |
| b | 0.020 | 0.039 | 0.51 | 0.99 |
| c | 0.012 | 0.029 | 0.30 | 0.74 |
| c2 | 0.045 | 0.065 | 1.14 | 1.65 |
| D | 0.330 | 0.380 | 8.38 | 9.65 |
| D1 | 0.260 | ----- | 6.60 | ----- |
| E | 0.380 | 0.420 | 9.65 | 10.67 |
| E1 | 0.245 | ----- | 6.22 | ----- |
| e | 0.100 BSC | ----- | 2.54 BSC | ----- |
| H | 0.575 | 0.625 | 14.60 | 15.88 |
| L | 0.070 | 0.110 | 1.78 | 2.79 |
| L1 | ----- | 0.066 | ----- | 1.68 |
| L2 | ----- | 0.070 | ----- | 1.78 |
| L3 | 0.010 BSC | ----- | 0.25 BSC | ----- |
| M | 0° | 8° | 0° | 8° |

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: INCHES

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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